Graphene quantum refrigerator

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Quantum refrigerators soak up heat energy from a low-temperature region and dump it into a higher temperature region using external work done on the system. Quantum refrigerators are useful in cooling down a system to very low temperatures. In this letter, we show that a monolayer of strained graphene can be used as a quantum refrigerator with an excellent coefficient of performance and large cooling power. The operating point at which it works best as a quantum refrigerator is derived and the effects of strain and temperature on graphene refrigerator are discussed.

1. INTRODUCTION

The efficacy of quantum refrigerators (QR’s) at the nanoscale has been made more than obvious in the past half decade [1]. From being useful in schemes for removal of excess heat in nanosystems to achieving low temperatures or in designing quantum computers they have been one of the most productive areas of research [2]. The thermoelectric figure of merit \( ZT \) of graphene is very small around 0.01-0.1 [4], which is much smaller than some of the most efficient thermoelectric materials, e.g., Bi\(_2\)Te\(_3\), see Refs. [3] [4]. The reason behind this small \( ZT \) factor is its large thermal conductance and absence of any band gap. In some recent works, this factor \( ZT \) has improved to a moderate value of around 2.5-3. This improvement in the thermoelectric figure of merit is attributed to doping graphene with isotopes [6] or nanoribbons [7] or disorder [5] or by nano-patternning the graphene surface [8]. A large \( ZT \) factor is required to generate high coefficient of performance (COP) for a QR. A large COP means the QR can use the electrical power to absorb heat energy from the cooler terminal more efficiently. Instead of doping as done in related works, we consider straining the graphene layer in order to generate high COP. In a previous work of ours [9], we have shown the potential use of a strained graphene sample to operate as a quantum heat engine. In this manuscript, we concentrate only on the refrigeration aspect of a strained graphene monolayer. Another important aspect of this paper is that it operates in the steady state transport regime. Quantum refrigerator’s (QR’s) which work for cyclic transport are also a major avenue of research. Examples of cyclic quantum refrigeration in literature can be seen in Refs. [10–12]. Advantage of cyclic quantum refrigeration over steady state quantum refrigeration is that cyclic QR’s are independent of the property of the working substance [12], i.e., the material characteristics, such as Carnot refrigerators, Otto refrigerators, while all steady state QR’s are dependent on the working substance. Cyclic QR’s are of two types- 1) reversible, 2) irreversible. Cyclic QR’s do have some disadvantages too. Cyclic reversible QR’s like Carnot or Otto refrigerators are based on reversible processes, thus to complete one full cycle they take infinite time, thereby, reducing the practical application of these refrigerators. Cyclic irreversible QR’s are dependent on irreversible processes which take much less time to complete one full cycle, however, the efficiency of these refrigerators is much reduced from the Carnot limit due to the dissipation within the system. On the other hand, examples of steady state QR’s can be seen in Refs. [13–15]. Steady state QR’s absorb heat from the cooler terminal by moving the microscopic particles like electrons, phonons or photons, rather than moving any microscopic part of the system (like quantum cyclic refrigerators). Since, steady state QR’s do not depend on the movement of the microscopic body part of the system, they can be much smaller in size than the cyclic QR’s. The disadvantage of steady state QR’s is that the efficiency in these systems can never reach the Carnot limit due to the dissipation, and joule heating which occurs within the system.

The rest of the paper is arranged as follows. In section 2 we describe the theory needed to calculate the thermoelectric figure of merit \( ZT \), Onsager coefficients, maximum COP and cooling power. The operating regime where our system works as a quantum refrigerator is also explained. Next in section 3 we describe our model of monolayer strained graphene which work for cyclic transport are also a major avenue of research. Examples of cyclic quantum refrigeration in literature can be seen in Refs. [10–12]. Advantage of cyclic quantum refrigeration over steady state quantum refrigeration is that cyclic QR’s are independent of the property of the working substance [12], i.e., the material characteristics, such as Carnot refrigerators, Otto refrigerators, while all steady state QR’s are dependent on the working substance. Cyclic QR’s are of two types- 1) reversible, 2) irreversible. Cyclic QR’s do have some disadvantages too. Cyclic reversible QR’s like Carnot or Otto refrigerators are based on reversible processes, thus to complete one full cycle they take infinite time, thereby, reducing the practical application of these refrigerators. Cyclic irreversible QR’s are dependent on irreversible

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too are affected. So, it is one of the outstanding challenges in quantum thermoelectrics to design an efficient QR to optimize these parameters effectively such that we get large COP and large cooling power. The difference between a quantum heat engine and QR is that in quantum heat engine one always needs a small thermal conductance to get a large efficiency at maximum output power, while for QR one needs a large thermal conductance for large cooling power. Of course here we are talking about electronic contribution to the thermal conductance to be large, phonon contribution to the thermal conductance has to be small otherwise it will decrease both the COP and the cooling power. To calculate the COP and cooling powers and to design a QR, first we need to calculate the thermoelectric properties of our system Seebeck, Peltier, electrical and thermal conductances. In linear transport regime the electrical and heat currents are related to the electric and thermal biases via the Onsager coefficients, which are written as-[17]-[19].

\[
\left( \begin{array}{c}
J^e \\
J^0
\end{array} \right) = \left( \begin{array}{cc}
L^{11} & L^{12} \\
L^{21} & L^{22}
\end{array} \right) \left( \begin{array}{c}
\mathcal{E} \\
\Delta \theta
\end{array} \right),
\]

(1)

where \(J^e\) and \(J^0\) define the electric and heat currents respectively, \(L_{ij}\) with \(i, j \in 1, 2\) denotes the Onsager coefficients. The Seebeck coefficient is defined as the voltage difference generated across the system due to an unit temperature difference applied. while Peltier coefficient is defined as the ratio of the heat current transmitting through the junctions to the electrical current passing through that junction. They are given as follows-

\[
S = -\frac{L^{12}}{L^{11}}, \quad \text{and} \quad P = \frac{L^{21}}{L^{11}}.
\]

(2)

The Onsager co-efficient matrix written in Eq. (1) linking electric and heat currents to the temperature difference \(\Delta \theta\) and applied voltage bias \(\mathcal{E}\) thus can be rewritten as [17][20],

\[
\left( \begin{array}{cc}
L^{11} & L^{12} \\
L^{21} & L^{22}
\end{array} \right) = \left( \begin{array}{cc}
L^0 & \mu T \\
L^1 & \mathcal{E}
\end{array} \right) \left( \begin{array}{cc}
L^1 & \mathcal{E} T \\
L^2 & \mathcal{E}^2 T
\end{array} \right),
\]

(3)

wherein,

\[
L^0 = G_0 \int_{-\pi/2}^{\pi/2} d\phi \cos \phi \int_{-\infty}^{\infty} d\epsilon \left( -\frac{\partial f}{\partial \epsilon} \right) \frac{|\epsilon|}{\hbar v_F} (\epsilon - \mu) \alpha T(\epsilon, \phi),
\]

(4)

here \(G_0 = (e^2/\hbar) (W/\pi^2)\), \(L^0 = G\) defines the conductance of system with width of sample-\(W\) [21], \(f\) the Fermi-Dirac distribution function, \(\phi\) defines the angle of incidence for electrons, \(T(\epsilon, \phi)\) is the electronic transmission probability through strained graphene layer and \(\mu\) the Fermi energy. Once we know the transmission probability\(T(\epsilon, \phi)\), we can calculate the Onsager coefficients’ \(L_{ij}\)’s as shown in Eq. (1). After calculating the Onsager coefficients, other quantities such as cooling power and COP can be calculated as follows. The cooling power [18], is defined as -

\[
J^0 = (L^{21} \mathcal{E} + L^{22} \Delta \theta)
\]

(5)

Our system of a strained graphene mono-layer is shown in Fig. 1. It works as a quantum refrigerator(QR) only when a net heat current is flowing from the cooler to hotter terminal making the colder terminal still more cooler, i.e., when it flows against the applied temperature bias \(\Delta \theta = \theta_1 - \theta_2\) and the net electrical current flows from higher potential bias to the lower bias, i.e., the external work is done on the system. Thus, if a temperature bias \(\Delta \theta\) is applied at the left terminal \((\theta_1 > \theta_2)\) and potential bias \(\mathcal{E}\) is applied at the right terminal \((\mathcal{E}_2 > \mathcal{E}_1)\), then both heat current and electrical current flow from right to left \((J^e < 0, J^Q < 0\) considering +x direction as the positive direction) for this system to work as a QR. The efficiency of a QR, i.e., how good it is in converting a stream of charged particles into carrying heat energy is called coefficient of performance (COP)[15][16]. COP of a QR is defined as the ratio of heat current absorbed from the hot reservoir to electrical power\(\mathcal{P}\) applied on the system, such that-

\[
\eta^r = \frac{J^Q}{\mathcal{P}}.
\]

(6)

where \(\mathcal{P}\), the electrical work done on the system, is defined as-

\[
\mathcal{P} = J^e \mathcal{E} = (L^{11} \mathcal{E} + L^{12} \Delta \theta) \mathcal{E}.
\]

(7)

The COP\(\eta^r\) is maximum when \(\frac{\partial \eta^r}{\partial \mathcal{E}} = 0\) and considering \(J^Q < 0\) and \(\mathcal{P} < 0\), we have-

\[
\mathcal{E} = \frac{L^{22}}{L^{21}} (-1 - \sqrt{\frac{L^{11} L^{22} - L^{12} L^{21}}{L^{11} L^{22}}} \mathcal{E}^2).
\]

(8)

The COP becomes maximum when the above relation Eq. (8) between the potential bias and thermal bias holds and thus the maximum COP is when-

\[
\eta^r_{\text{max}} = \frac{\eta^c}{\sqrt{\frac{1}{\sqrt{3}} + 1}} = \frac{\sqrt{ZT + 1} - 1}{\sqrt{ZT + 1} + 1},
\]

(9)

with, \(J^0(\eta^r_{\text{max}})\) is the cooling power when COP is maximum. The thermoelectric figure of merit \(ZT\) is defined as-

\[
ZT = \frac{G \alpha^2 T}{\kappa},
\]

(11)

while thermal conductivity is-

\[
\kappa = \frac{L^{11} L^{22} - L^{12} L^{21}}{L^{11}},
\]

(12)

In systems with broken time reversal(TR) symmetry, the upper bound on the refrigerator efficiency \(\eta^r_{\text{max}}\) decreases from \(\eta^c\) as the asymmetric parameter \(x = \theta L^{12}/L^{21}\) deviates from one[22][23]. In systems with TR symmetry preserved, the asymmetric parameter \(x\) is unity, and upper bound on the corresponding maximum efficiency\(\eta^r_{\text{max}}\) equals \(\eta^c\). This is the advantage of systems with TR symmetry preserved, that they can work as highly efficient QR’s with almost Carnot efficiency. However, for systems with broken TR symmetry working as QR, the upper bound is always less than \(\eta^c\) (the Carnot limit).
transmission of electrons gets shifted in the two valley as a function of incident angle in two opposite directions. However, the total transmission which is sum over all the incident angles remains same for both the valleys $K$ and $K'$. The Hamiltonian for the system for $K$ and $K'$ valley is-

$$\mathcal{H}_K = \hbar v_f \sigma(k - s), \quad \mathcal{H}_K' = -\hbar v_f \sigma\,'(k + s). \quad (13)$$

Considering Landau gauge, one can replace the strain with pseudo magnetic vector potential $A = (0, \pm A_z)$, where '+' and '-' signs denote $K$ and $K'$ valleys respectively. Thus, strain-$s = \frac{A_z}{\hbar v_f}[\Theta(x) - \Theta(x - L)]$, with $v_f$-the Fermi velocity, $\sigma = (\sigma_x, \sigma_y)$ are Pauli matrices operating on the sub-lattices A and B with $\sigma\,'$ being complex conjugation, $\Theta$-the step function and $k = (k_x, k_y)$-the 2D wave vector. From Hamiltonian, Eq. (13), we get the wave equation for valley-

$$\hbar v_f(-i\alpha x - \beta y - is)\psi_B = E\psi_A,$$

$$\hbar v_f(-i\alpha x + \beta y + is)\psi_A = E\psi_B, \quad (14)$$

where $\psi_A$ and $\psi_B$ are the wave functions at A and B sublattices respectively. Using Eq. (14), one can calculate the transmission probability for ballistic transport in a monolayer of strained graphene sample, which we show in the next subsection.

### 3.2. Wave functions and boundary conditions

In Fig. 1(bottom) an electron is incident from the left side of the interface between two regions (region I and region II) with energy $\epsilon$, then either it can reflect back to region I or it can transmit into region II depending on its energy and angle of incidence. We define three regions I, II and III as normal graphene ($x < 0$), strained graphene ($0 < x < L$) and normal graphene ($x > L$) respectively. The wave functions of electrons in the three regions for A and B sublattices in $K$ valley are as follows.-

For $x < 0$-

$$\begin{bmatrix} \psi_A^I(x, y) \\ \psi_B^I(x, y) \end{bmatrix} = \begin{bmatrix} (ae^{ik_x x} + be^{-ik_x x}) \\ (ae^{ik_x x + i\phi} - be^{-ik_x x - i\phi}) \end{bmatrix} e^{ik_y y}, \quad (15)$$

in strained graphene layer $0 < x < L$-

$$\begin{bmatrix} \psi_A^I(x, y) \\ \psi_B^I(x, y) \end{bmatrix} = \begin{bmatrix} (ae^{ik_x x} + be^{-ik_x x}) \\ (ae^{ik_x x + i\phi} - be^{-ik_x x - i\phi}) \end{bmatrix} e^{ik_y y}, \quad (16)$$

and for $x > L$-

$$\begin{bmatrix} \psi_A^I(x, y) \\ \psi_B^I(x, y) \end{bmatrix} = \begin{bmatrix} te^{ik_x x} \\ te^{ik_x x + i\phi} \end{bmatrix} e^{ik_y y}, \quad (17)$$

where $k_x = (\epsilon / \hbar v_f) \cos \theta$ and $k_y = (\epsilon / \hbar v_f) \sin \theta$ are the $x$ and $y$ components of momentum wave vector in normal graphene. In strained graphene $k_x$ is replaced with $q_x = \sqrt{(\epsilon / \hbar v_f)^2 - (k_y - s)^2} = (\epsilon / \hbar v_f) \cos \theta$ and $k_y - s = (\epsilon / \hbar v_f) \sin \theta$, $\theta$ being the refraction angle in the strained region as shown in Fig. 1(bottom) and also satisfies $\tan \theta = (k_y - s)/q_x$. Using wave functions- Eqs. (15-17), and applying boundary conditions at $x = 0$-

$$\psi_B^I(x = 0) = \psi_B^I(x = 0), \quad \psi_A^I(x = 0) = \psi_A^I(x = 0), \quad (18)$$

Figure 1. Top: Monolayer graphene with uniaxial strain applied in the $x$ direction. The middle portion is strained region while the two side portions are normal graphene regions. Voltages $V_1$ and $V_2$ are applied to the two terminals which are at temperatures $\theta_1$ (left side) and $\theta_2$ (right side) respectively. Bottom: An electron is incident on the interface between normal graphene and strained graphene with incident angle $\phi$ and refracted to strained region with refraction angle $\theta$. To work as a QR, the relation between potential bias $\mathcal{E}$ and thermal bias $\Delta \theta$ has to be such that the electric current $J^e < 0$ and the heat current $J^q < 0$, i.e., both electric and heat current flow from the cooler to the hotter region. Solving these two equations $J^e < 0$ and $J^q < 0$ we get the operating regime for QR’s as $\mathcal{E} < -(\kappa/(GP)) \Delta \theta$. This defines the parametric space in which our graphene system acts as a QR. In the next section, we give a detailed description of our model.

**3. MODEL**

**3.1. Hamiltonian**

Graphene is a semi-metal with zero band gap. It is a carbon allotrope with carbon atoms arranged in a single layer of honeycomb lattice with inter penetrating triangular sublattices. An uniaxial strain is introduced in our model of monolayer graphene sheet lying in the $xy$ plane via stretching or compressing the region between $x = 0$ and $x = L$ as shown in Fig. 1. The region to the left and right of this strained region is normal graphene. To design our model as a quantum refrigerator we apply thermal bias $\Delta \theta$ at the left contact and a potential bias $\mathcal{E}$ at the right contact. At steady state, electric current $J^e$ and heat currents $J^q$ flow between the reservoirs. In the strained region, electrons gets refracted away from the normal (perpendicular to the interface) in one valley (say $K$) and refracted towards the normal in the other valley ($K'$). The
and at \( x = L \),
\[
\psi_B^2(x = L) = \psi_A^2(x = L), \quad \psi_B^2(x = L) = \psi_B^2(x = L). \quad (19)
\]
Solving Eqs. (18)\,(19) we derive the electronic transmission probability for \( K \) valley-
\[
T(\epsilon, \phi) = \frac{1}{\cos^2[q_sL] + \sin^2[q_sL]} (\frac{1 - \sin(\phi) \sin(\phi')}{\cos(\phi) \cos(\phi')})^2.
\] (20)

Similarly, one can derive the transmission function by solving the Hamiltonian for \( K' \) valley as in Eq. (13), using the same boundary conditions and substituting \( \phi \to -\phi, s \to -s \). The total electronic transmission probability \( T(\epsilon) \) is the sum of \( K \) and \( K' \) valley transmissions. It is apparent that although transmission \( T(\epsilon, \phi) \) differs in \( K \) and \( K' \) valley transmissions. It is apparent that although transmission \( T(\epsilon, \phi) \) differs in \( K \) and \( K' \) valley transmission.

4. RESULTS AND DISCUSSION

To design an efficient quantum refrigerator (QR), we not only need large Seebeck coefficient but also a large Peltier coefficient. A large Peltier coefficient means that a stream of electrons or holes carrying current from one terminal to another not only transport charge but also heat energy along with them. Thus, decreasing the temperature of the colder terminal. In any two terminal system, the time reversal symmetry (TR symmetry) is always conserved. This implies that the Seebeck and Peltier coefficient are related by the relation \( P = \theta S \) (due to the Onsager reciprocity relation \( L_{21} = \theta L_{12} \)). In Figs. 3 (a, b) we plot Peltier coefficient. The Seebeck coefficient can be inferred from these plots via \( S = P/\theta \). Breaking TR symmetry leads to the upper bound of COP reducing from Carnot limit of efficiency, while in our system due to the conservation of TR symmetry the upper bound of COP can in principle reach the maximum Carnot limit. We first (in Fig. 2) plot the electrical conductances and see that it increases with increasing Fermi energy, see Fig. 2(a). We also see in Fig. 2(a), that increasing the length of the strained layer shifts the transport of incident electrons with low energy into the evanescent regime, and thus opens a conduction gap close to the Dirac point, while it remains almost unaffected at higher Fermi energies. Increasing strain can make the transmission of an electron at particular incident angle to be unity due to Klein effects\,[24], however, the overall transmission sum over all the incident angle reduces with strain, see Fig. 2(b). This reduction of electrical conductance is almost independent of the length of the strained region. In Figs. 3(a) and (b), we see that increasing either strain or the length of the strained region makes electrical conduction slowly to shift to the evanescent regime, then electrical conduction reduces enabling Peltier coefficient to increase since it is inversely proportional to conductance. This means electrons carry larger heat energy along with them and thus we see a corresponding increase in the Peltier coefficient. As strain is increased more, the electrical transmission \( T(\epsilon, \phi) \) shifts completely to the evanescent regime, and Peltier coefficient increases much more. That is the reason the COP of our model is huge for larger strains and large lengths of the strained region, see Fig. 4(a), while the cooling power decreases, see Fig. 4(b). The positive Peltier coefficient for Fermi energies greater than the Dirac point energy observed in Fig. 3(b) is attributed to the increased electronic contribution while for Fermi energies below the Dirac point energy the negative Peltier coefficient is attributed to increasing hole contribution. The peak in Peltier coefficient observed near the Dirac point both positive as well as negative is due to the imperfect cancellation of electron and hole contributions to the Peltier coefficient, while at energies at much higher or much lower than the Dirac point the electronic and hole contribution to the Peltier coefficient almost cancel leading to a vanishing Peltier coefficient.

In Fig. 5(a), we see that COP of our model is not temperature independent, the COP reduces as temperature decreases. On the other hand the cooling power is almost temperature independent, see Fig. 5(b). In Fig. 6(a), we see that two peaks appear in the COP as function of Fermi energy. The first peak is present even at zero strain, that means strain is not a source of this peak. This peak appears close to the Dirac point and is due to the imbalance in the contribution of hole and electrons towards the Peltier coefficient as explained above. The second peak increases with increasing strain and vanishes for zero strain, that means strain is the sole reason behind this peak. The reason behind the appearance of the second peak
Our proposal of a quantum refrigerator based on a strained monolayer graphene layer is experimentally realizable. Many theoretical, see Ref. [26, 29], as well as many experimental works[27, 28] deal with uniaxial strain in monolayer graphene system. Thus, realizing strain in graphene system would not be much difficult. Also, the amount of strain used in our system is very small. One can apply a maximum 20% strain (540 meV) without opening a band gap, while in our paper the optimum strain applied at ‘Q’ point is 30 meV (1% strain). Numerical values of all the other parameters used in our paper are also physically realizable and used in other works, see Refs. [21, 26]. Thus, the applied aspect of our work is very much realizable.

6. CONCLUSION AND PERSPECTIVE ON RELATED WORKS

In this manuscript a strained monolayer graphene sheet has been designed to work as a quantum refrigerator (QR). The maximum coefficient of performance of our QR is around 0.95 \( \eta_c^* \) (see Fig. 7). This large COP seen in our paper occurs at strain \( s = 300 \) meV, which is 11% strain, much less than the maximum 20% strain (540 meV) and thus does not open any band gap within our system. The maximum cooling power possible with our QR is 12 \( (k_B^2 \Delta \theta) / \hbar \) (see Fig. 6(b)). However, we note that the maximum values of coefficient of performance and of cooling power seen in our QR do not correspond to same set of parameters, the optimum values of coefficient of performance as well as cooling power are 0.10\( \eta_c^* \) and 2 \( (k_B^2 \theta) / \hbar \) and these occur at identical parametric values, i.e., the ‘Q’ point. Steady state quantum refrigeration as seen in this manuscript in strained graphene is a nascent topic. Not many works[13, 14] have addressed the topic of steady state quantum refrigeration. In the following we briefly address these works mentioning their advantages and disadvantages vis-a-vis our work. Ref. [13] discusses a three terminal quantum dot refrigerator, wherein the maximum COP and cooling power are 0.4\( \eta_c^* \) and 0.87 \( (k_B^2 \theta) / \hbar \) respectively (see Fig. 9 of Ref. [13]). Thus, we see while maximum COP delivered is larger than that seen at the ‘Q’ point of our QR, the cooling power at that max-

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**Figure 4.** (a) COP in units of \( \eta_c^* \) at temperature \( \theta = 30K \) for various lengths of strained layer with width \( W = 20nm \) and Fermi energy \( \mu = 29.6meV \). (b) Cooling power in units of \( (k_B^2 \theta \Delta \theta) / \hbar \) at \( \theta = 30K \) for various lengths of the strained layer with width \( W = 20nm \) and Fermi energy \( \mu = 29.6meV \).

**Figure 5.** (a) COP in units of \( \eta_c^* \) at different temperatures with \( L=60 \) nm, width \( W = 20 \) nm and Fermi energy \( \mu = 29.6 \) meV. (b) Cooling power in units of \( (k_B^2 \theta \Delta \theta) / \hbar \) for various temperatures with \( L=60 \) nm, width \( W = 20 \) nm and Fermi energy \( \mu = 29.6 \) meV.

**Figure 6.** (a) COP in units of \( \eta_c^* \) at \( \theta = 30K \) at different strains with \( L = 60nm \), width \( W = 20nm \), (b) Cooling power in units of \( (k_B^2 \theta \Delta \theta) / \hbar \) at \( \theta = 30K \) for various strains with \( L = 60nm \), width \( W = 20nm \).
maximum COP is smaller. In Ref. [14], it has been shown that a magnon driven quantum dot refrigerator has COP 0.2\(\eta^r_c\) while again the cooling power seen 0.8(\(k_B^2\theta\))/\(h\) is much smaller than that seen at the ‘Q’ point of our system. Unfortunately, Refs. [13] [14] do not discuss the ‘Q’ point for their refrigerators. Further, Refs. [13] [14] consist of a three terminal system, which by design has an advantage over a two terminal system since in a three terminal system heat and electric currents can flow between separate terminals, so one can have better control over these parameters. Similarly, we propose that in a quantum refrigerator based on three terminal strained graphene system the performance can be increased further, which can be the subject of another manuscript.

**ACKNOWLEDGMENTS**

This work was supported by funds from Science & Engineering research Board, New Delhi, Govt. of India, Grant No. EMR/2015/001836.